

# 2SB1574

## Silicon PNP epitaxial planar type

For low-frequency output amplification

### ■ Features

- Possible to solder radiation fin directly to printed circuit board
- Type with universal characteristics
- High collector-base voltage (Emitter open)  $V_{CBO}$
- High collector-emitter voltage (Base open)  $V_{CEO}$
- Large collector current  $I_C$

### ■ Package

- Code  
U-G2
- Pin Name  
1: Base  
2: Collector  
3: Emitter

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-2	A
Peak collector current	$I_{CP}$	-3	A
Collector power dissipation	$P_C$	10	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -10 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Forward current transfer ratio	$h_{FE1}^*$	$V_{CE} = -2 \text{ V}, I_C = -200 \text{ mA}$	120		340	—
	$h_{FE2}$	$V_{CE} = -2 \text{ V}, I_C = -1 \text{ A}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$		-0.2	-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$		-0.85	-1.20	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_C = -50 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		45	60	pF

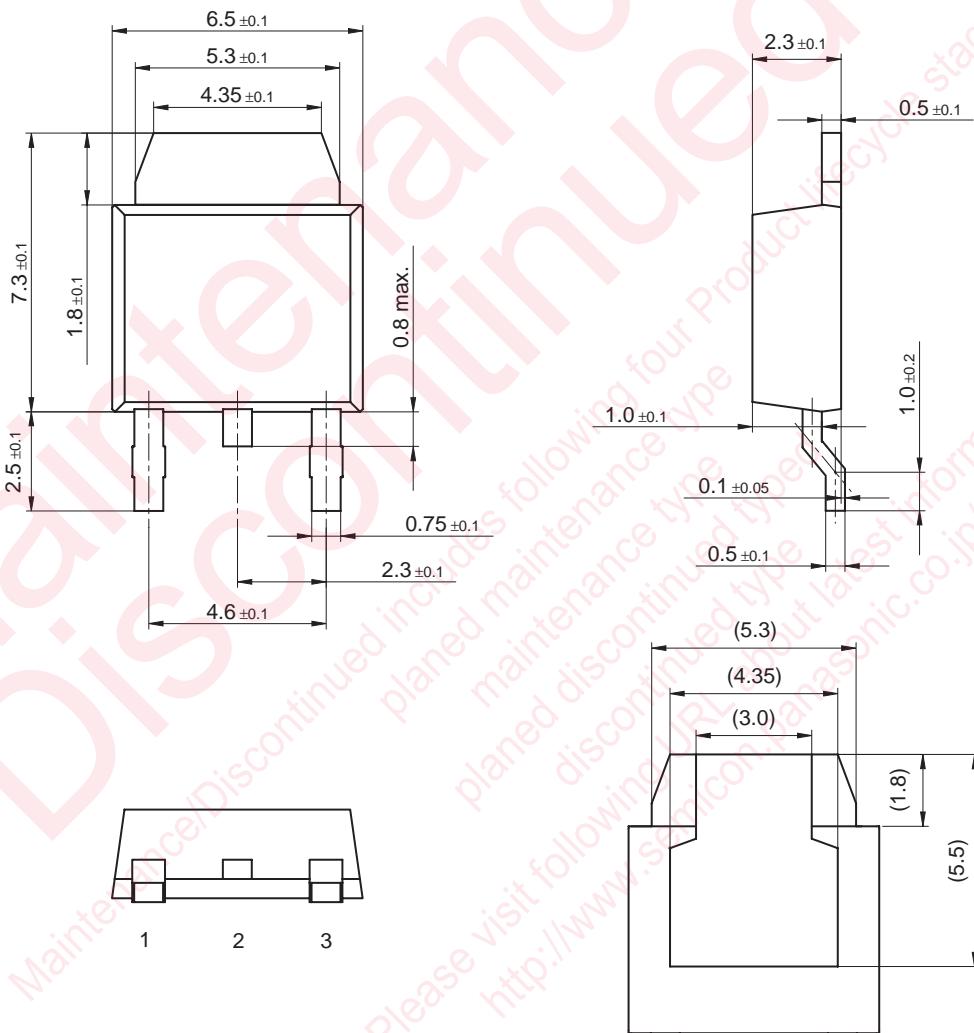
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	R	S
$h_{FE1}$	120 to 240	170 to 340

U-G2

Unit: mm



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